



P-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

V _{(BR)DSS}	R _{DS(on) max}	Ι _D T _A = +25°C
-12V	31mΩ@ V _{GS} = -4.5V	-5.2A
-120	45mΩ@ V _{GS} =-2.5V	-4.3A

Description

This new generation MOSFET has been designed to minimize the onstate resistance ($R_{DS(ON)}$) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

Applications

- DC-DC Converters
- Power management functions
- Analog Switch

Features and Benefits

- Low On-Resistance
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- ESD Protected Up To 3kV
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- PPAP Capable (Note 4)

Mechanical Data

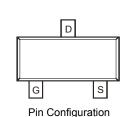
- Case: SOT23
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram
- Terminals: Finish Matte Tin annealed over Copper leadframe.
 Solderable per MIL-STD-202, Method 208 (3)
- Weight: 0.0072 grams (approximate)

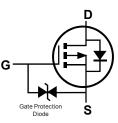




SOT23

Top View





Internal Schematic

Ordering Information (Note 5)

Part Number	Compliance	Case	Packaging
DMP1045UQ-7	Automotive	SOT-23	3,000/Tape & Reel

Notes: 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.

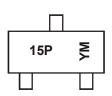
2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.

3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

4. Automotive products are AEC-Q101 qualified and are PPAP capable. Automotive, AEC-Q101 and standard products are electrically and thermally the same, except where specified. For more information, please refer to http://www.diodes.com/quality/product_grade_definitions/.

5. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information



15P = Marking Code YM = Date Code Marking Y or = Year (ex: A = 2013) M = Month (ex: 9 = September)

Date Code Key

Date Code Key					-							
Year	20	13	20	14	20	15	20	16	20	17	20	18
Code	A	Ą	E	3	(2	[)	E		F	=
	-							_	-	-		
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D



Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Units		
Drain-Source Voltage		V _{DSS}	-12	V	
Gate-Source Voltage			V _{GSS}	±8	V
Continuous Drain Current (Note 6) V_{GS} = -4.5V	Steady State	T _A = +25°C T _A = +70°C	ID	-4.0 -3.1	А
Continuous Drain Current (Note 6) V_{GS} = -2.5V	Steady State	T _A = +25°C T _A = +70°C	ID	-3.3 -2.6	A
Continuous Drain Current (Note 7) V_{GS} = -4.5V	Steady State	T _A = +25°C T _A = +70°C	ID	-5.2 -4.2	А
Continuous Drain Current (Note 7) V_{GS} = -2.5V	Steady State	T _A = +25°C T _A = +70°C	ID	-4.3 -3.4	А
Maximum Continuous Body Diode Forward Current		Is	-2	A	
Pulsed Drain Current (10µs pulse, duty cycle=1%) (IDM	-40	A	

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Units
Total Power Dissipation (Note 6)	PD	0.8	W
Thermal Resistance, Junction to Ambient (Note 6)	R _{0JA}	168	°C/W
Total Power Dissipation (Note 7)	PD	1.3	W
Thermal Resistance, Junction to Ambient (Note 7)	$R_{ ext{ heta}JA}$	99	°C/W
Thermal Resistance, Junction to Case (Note 7)	$R_{ ext{ heta}Jc}$	14.8	°C/W
Operating and Storage Temperature Range	T _{J,} T _{STG}	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 8)						
Drain-Source Breakdown Voltage	BV _{DSS}	-12	—	_	V	V _{GS} = 0V, I _D = -250µA
Zero Gate Voltage Drain Current $T_J = +25^{\circ}C$	I _{DSS}	_	—	-1.0	μA	V _{DS} = -12V, V _{GS} = 0V
Gate-Source Leakage	IGSS	_	_	±10	μA	V _{GS} = ±8V, V _{DS} = 0V
ON CHARACTERISTICS (Note 8)						
Gate Threshold Voltage	V _{GS(th)}	-0.3	-0.55	-1.0	V	V_{DS} = V_{GS} , I_D = -250 μ A
			26	31		V _{GS} = -4.5V, I _D = -4.0A
Static Drain-Source On-Resistance	R _{DS(ON)}	_	31	45	mΩ	V _{GS} = -2.5V, I _D = -3.5A
			45	75		V _{GS} = -1.8V, I _D = -2.7A
Forward Transfer Admittance	Y _{fs}	_	12	_	S	$V_{DS} = -5V, I_D = -4A$
Diode Forward Voltage	V _{SD}	_	-0.6	_	V	V _{GS} = 0V, I _S = -1A
DYNAMIC CHARACTERISTICS (Note 9)						
Input Capacitance		_	1357	-	pF	
Output Capacitance	Coss	_	504	-	pF	V _{DS} = -10V, V _{GS} = 0V f = 1.0MHz
Reverse Transfer Capacitance	Crss	_	235	_	pF	
Gate Resistnace	Rg	_	14.1	_	Ω	V _{DS} = 0V, V _{GS} = 0V, f = 1.0MHz
SWITCHING CHARACTERISTICS (Note 9)						
Total Gate Charge	Qg	_	15.8	_	nC	
Gate-Source Charge	Q _{gs}	_	2.0	_	nC	V_{GS} = -4.5V, V_{DS} = -10V, I_D = -4A
Gate-Drain Charge	Q _{gd}	_	3.9	_	nC	
Turn-On Delay Time	t _{D(on)}	_	15.7		ns	
Turn-On Rise Time	tr		23.3		ns	V _{DS} = -10V, V _{GS} = -4.5V,
Turn-Off Delay Time	t _{D(off)}		91.2		ns	R_L = 2.5Ω, R_G = 3.0Ω
Turn-Off Fall Time	t _f		106.9		ns	7

Notes: 6. Device mounted on FR-4 PC board, with minimum recommended pad layout, single sided.

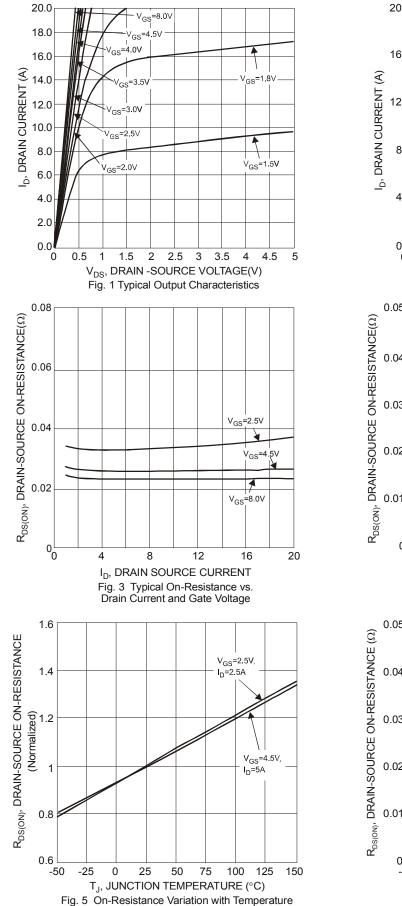
7. Device mounted on FR-4 substrate PC board, 2oz copper, with thermal vias to bottom layer 1inch square copper plate

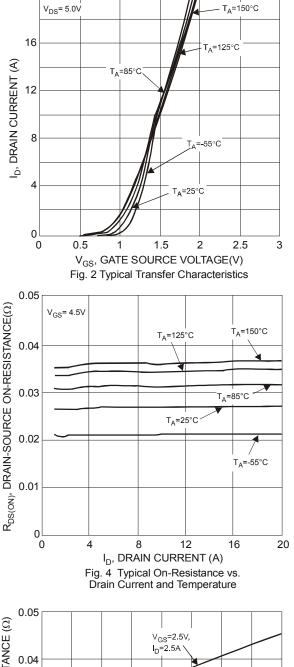
8 Short duration pulse test used to minimize self-heating effect.

9. Guaranteed by design. Not subject to production testing.



DMP1045UQ





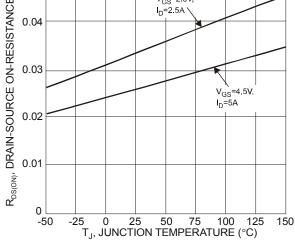
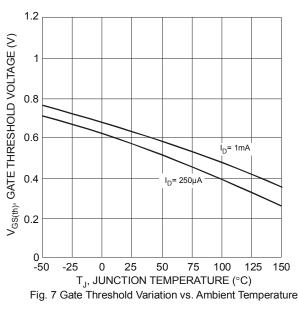


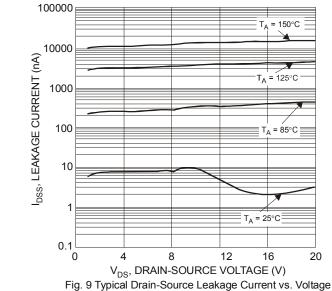
Fig. 6 On-Resistance Variation with Temperature

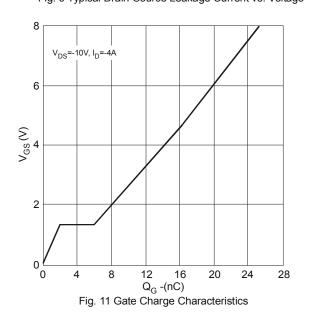
NEW PRODUCT

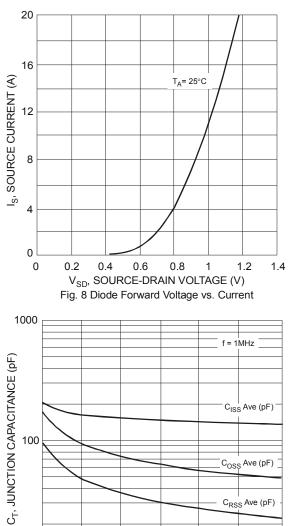
DMP1045UQ Document number: DS36874 Rev. 1 - 2











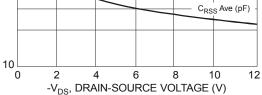
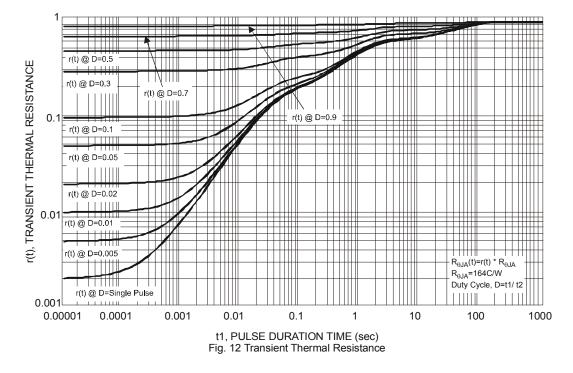


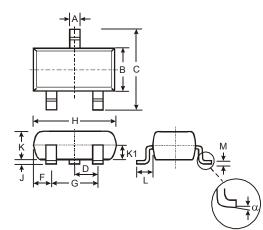
Fig. 10 Typical Junction Capacitance





Package Outline Dimensions

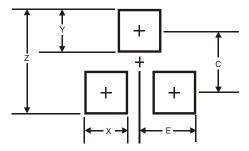
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for latest version.



	SOT23							
Dim	Min	Max	Тур					
Α	0.37	0.51	0.40					
В	1.20	1.40	1.30					
С	2.30	2.50	2.40					
D	0.89	1.03	0.915					
F	0.45	0.60	0.535					
G	1.78	2.05	1.83					
н	2.80	3.00	2.90					
J	0.013	0.10	0.05					
κ	0.903	1.10	1.00					
K1	-	-	0.400					
L	0.45	0.61	0.55					
М	0.085	0.18	0.11					
α	0°	8°	-					
All	All Dimensions in mm							

Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for latest version.



Dimensions	Value (in mm)
Z	2.9
Х	0.8
Y	0.9
С	2.0
E	1.35



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